Application Data Sh et

Inventor Information

Inventor One Given Name:

Family Name: Name Suffix:

Postal Address Line One

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Postal or Zip Code:

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Application Information

Title Line One:

Title Line Two:

Title Line Three: Title Line Four:

Title Line Five:

Total Drawing Sheets:

Formal Drawings?: **Application Type:**

Docket Number.

REFERENCE VOLTAGE GENERATION THE

CIRCUIT FOR SEMICONDUCTOR MEMORY

DEVICE, MEMORY READING CIRCUIT INCLUDING SAME, AND ELECTRONIC

INFORMATION DEVICE INCLUDING THE SAME

14

Yes

Utility

299002054200

Representative Information

Representative Customer Number:

25226

Continuity Information

This application is a: > Application One:

Filing Date:

which is a:

>>Application Two:

Filing Date:

which is a:

>>>Application Three:

Filing Date:

Prior Foreign Applications

Foreign Application One: 2001-057499

Filing Date: March 1, 2001

Country: Japan Priority Claimed: Yes